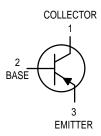
Low Noise Transistors PNP Silicon



MAXIMUM RATINGS

Rating	Symbol	BC559	BC560	Unit		
Collector-Emitter Voltage	VCEO	-30	-45	Vdc		
Collector-Base Voltage	VCBO	-30	-50	Vdc		
Emitter-Base Voltage	VEBO	-5.0		Vdc		
Collector Current — Continuous	IC	-100		mAdc		
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0		mW mW/°C		
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12				Watt mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150		°C		

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{ heta}$ JC	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Breakdown Voltage (I _C = -10 mAdc, I _B = 0)	BC559 BC560	V(BR)CEO	-30 -45	_ _	_ _	Vdc
Collector-Base Breakdown Voltage (I _C = -10 μAdc, I _E = 0)	BC559 BC560	V(BR)CBO	-30 -50			Vdc
Emitter-Base Breakdown Voltage (I _E = -10 μAdc, I _C = 0)		V(BR)EBO	-5.0	_	_	Vdc
Collector Cutoff Current $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0)$ $(V_{CB} = -30 \text{ Vdc}, I_{E} = 0, T_{A} = +125^{\circ}\text{C})$		ICBO	_ _	_ _	-15 -5.0	nAdc μAdc
Emitter Cutoff Current (V _{EB} = -4.0 Vdc, I _C = 0)		IEBO	_	_	-15	nAdc

BC559, B, C BC560C



BC559, B, C BC560C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Тур	Max	Unit	
ON CHARACTERISTICS						
DC Current Gain $ (I_{C} = -10 \ \mu Adc, \ V_{CE} = -5.0 \ Vdc) \\ (I_{C} = -2.0 \ mAdc, \ V_{CE} = -5.0 \ Vdc) \\ (I_{C} = -2.0 \ mAdc, \ V_{CE} = -5.0 \ Vdc) \\ BC559B \\ BC559C/560C \\ BC559$	hFE	100 100 180 380 120	150 270 290 500	— 460 800 800	_	
Collector-Emitter Saturation Voltage (I _C = -10 mAdc, I _B = -0.5 mAdc) (I _C = -10 mAdc, I _B = see note 1) (I _C = -100 mAdc, I _B = -5.0 mAdc, see note 2)	VCE(sat)	_ _ _	-0.075 -0.3 -0.25	-0.25 -0.6 	Vdc	
Base–Emitter Saturation Voltage (IC = -100 mAdc, IB = -5.0 mAdc)	V _{BE(sat)}	_	-1.1		Vdc	
Base–Emitter On Voltage $ \begin{aligned} &(I_C = -10 \; \mu\text{Adc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ &(I_C = -100 \; \mu\text{Adc}, \; V_{CE} = -5.0 \; \text{Vdc}) \\ &(I_C = -2.0 \; \text{mAdc}, \; V_{CE} = -5.0 \; \text{Vdc}) \end{aligned} $	VBE(on)	— — —0.55	-0.52 -0.55 -0.62	_ _ _ _0.7	Vdc	
SMALL-SIGNAL CHARACTERISTICS Current-Gain — Bandwidth Product	fT		250	_	MHz	
$(I_{C} = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$ Collector–Base Capacitance $(V_{CB} = -10 \text{ Vdc}, I_{E} = 0, f = 1.0 \text{ MHz})$	C _{cbo}	_	2.5	_	pF	
Small–Signal Current Gain (I _C = -2.0 mAdc, V _{CE} = -5.0 V, f = 1.0 kHz) BC559B BC559C/BC560C	h _{fe}	240 450	330 600	500 900	_	
Noise Figure (I _C = $-200~\mu$ Adc, V _{CE} = $-5.0~V$ dc, R _S = $2.0~k\Omega$, f = $1.0~kHz$) (I _C = $-200~\mu$ Adc, V _{CE} = $-5.0~V$ dc, R _S = $100~k\Omega$, f = $1.0~kHz$, Δ f = $200~kHz$)	NF ₁ NF ₂		0.5 —	2.0 10	dB	

NOTES:

^{1.} I_B is value for which I_C = -11 mA at V_{CE} = -1.0 V. 2. Pulse test = $300 \ \mu s$ – Duty cycle = 2%.

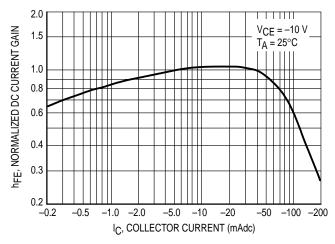


Figure 1. Normalized DC Current Gain

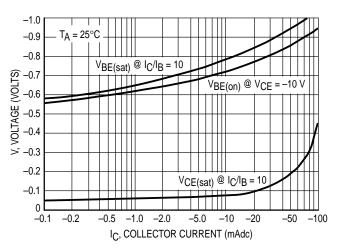


Figure 2. "Saturation" and "On" Voltages

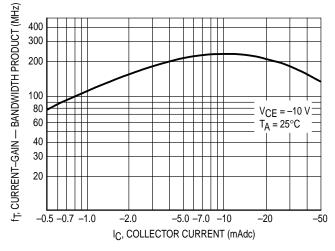


Figure 3. Current-Gain — Bandwidth Product

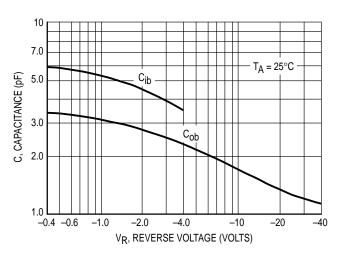


Figure 4. Capacitance

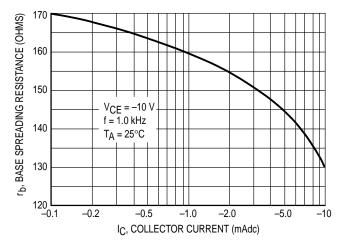
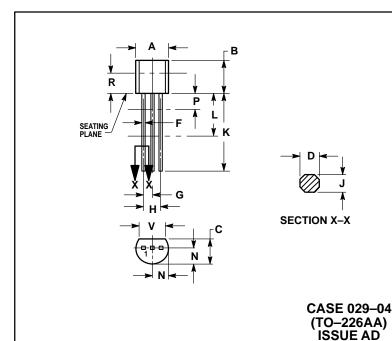


Figure 5. Base Spreading Resistance

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100		2.54	
R	0.115		2.93		
V	0.135		3 43		

STYLE 17:

PIN 1. COLLECTOR

2. BASE

3. EMITTER

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